



YJQ40G10AQ

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	100V
I_D	40A
$R_{DS(ON)}$ (at V_{GS}	

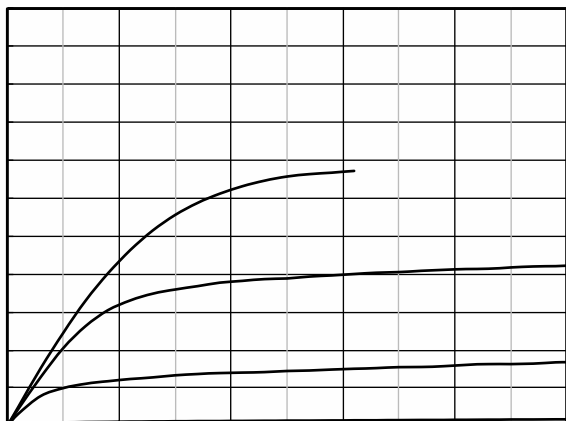
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Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max
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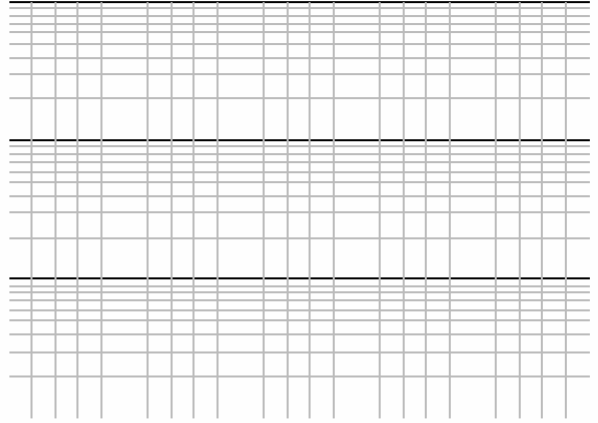
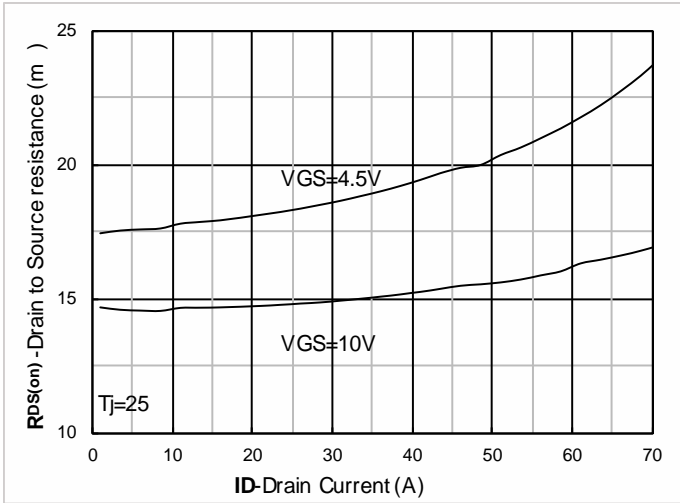


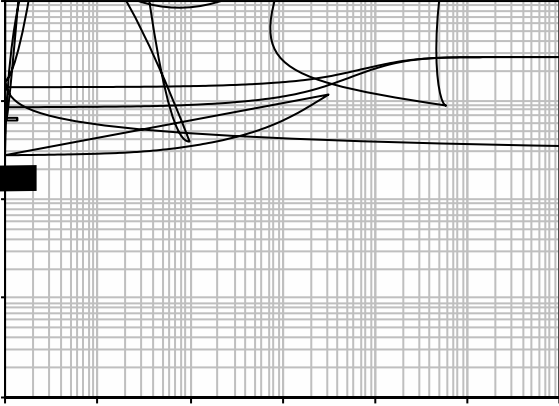
Typical Electrical and Thermal Characteristics Diagrams





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Test Circuits & Waveforms

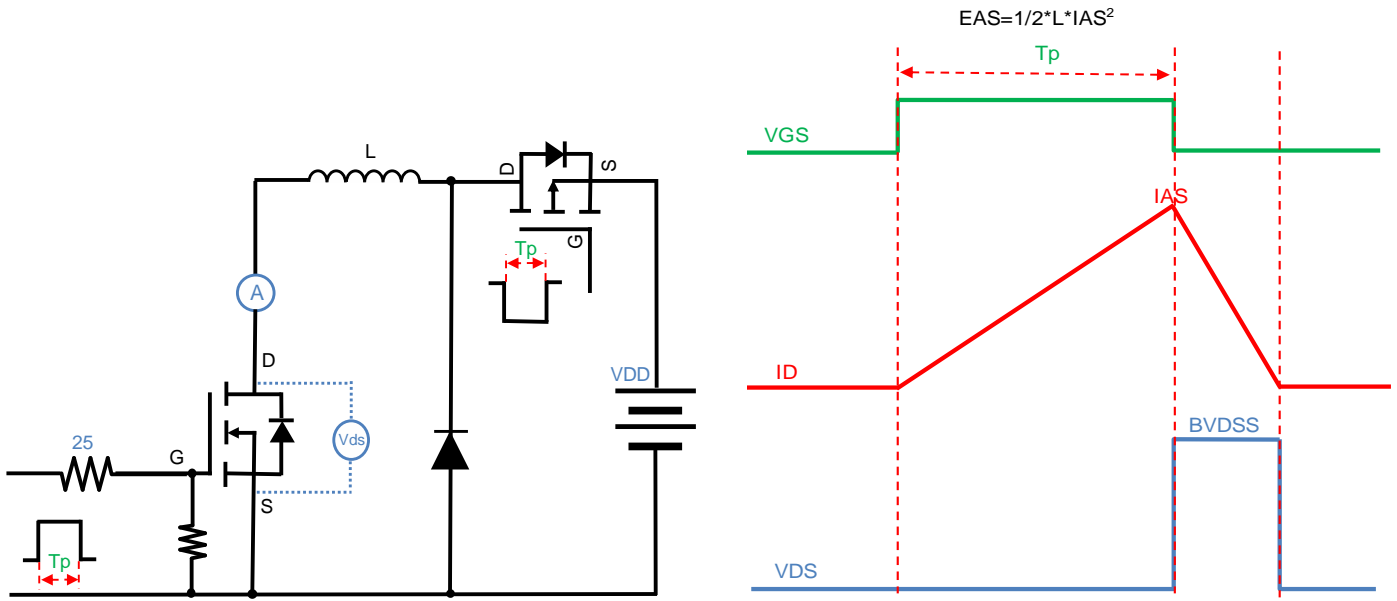
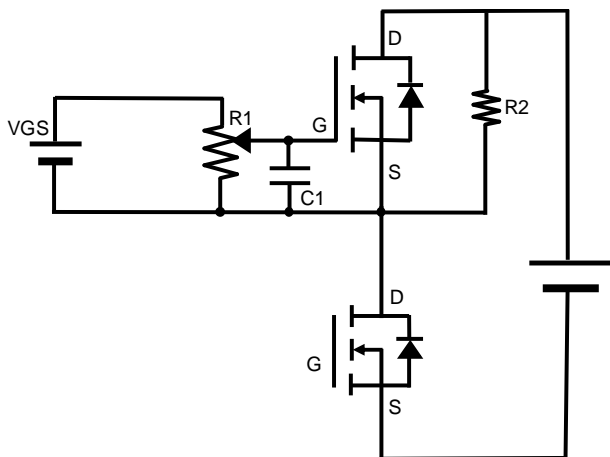
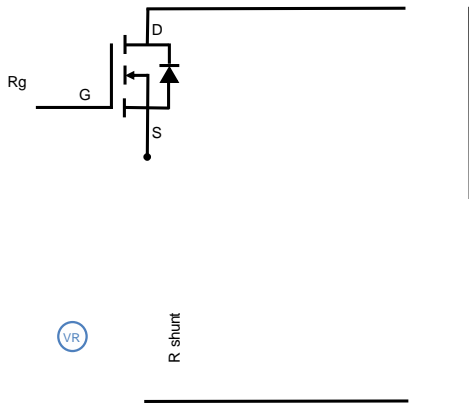


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform





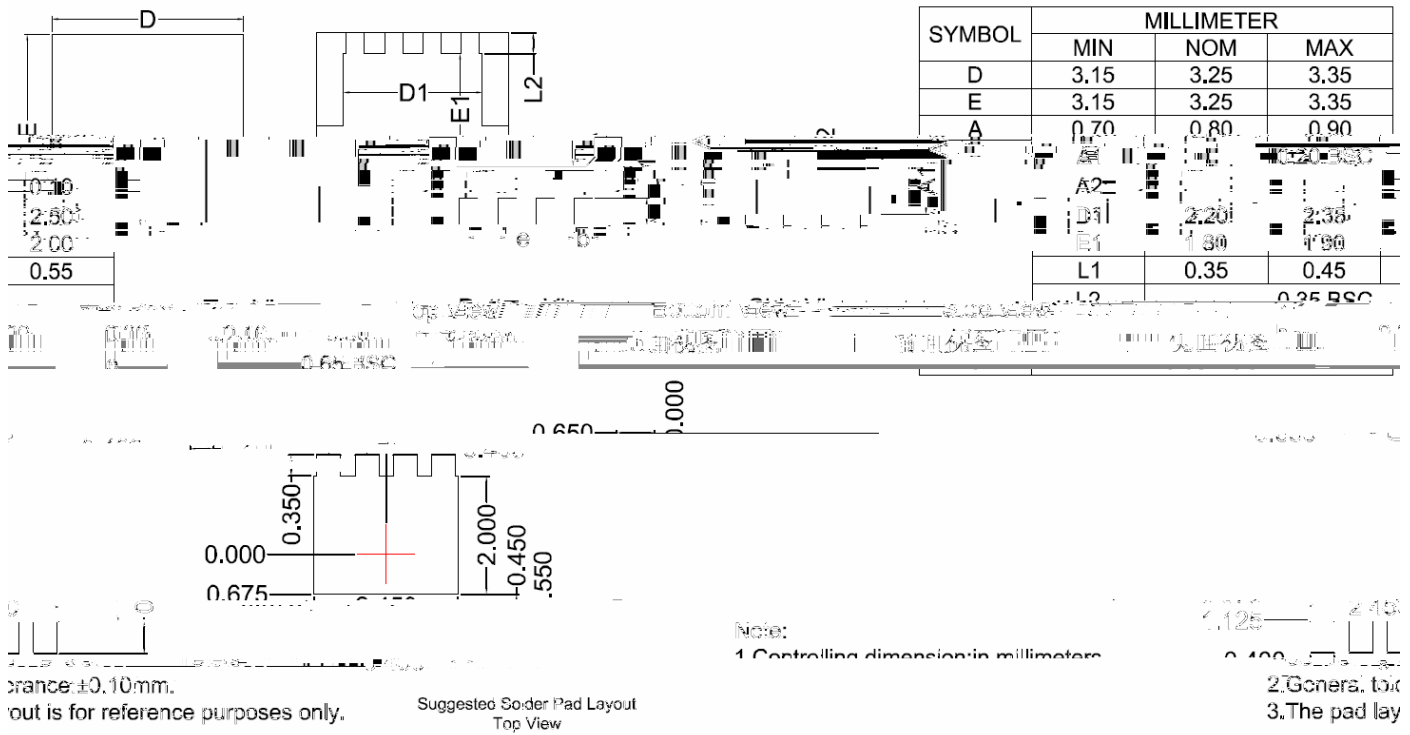
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DFN3333-8L Package information





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